IN THE CLAIMS:

The following is a complete listing of the claims in this application, reflects all changes currently being made to the claims, and replaces all earlier versions and all earlier listings of the claims:

Claims 1-12. (Canceled)

Claim 13. (Currently Amended) [[The]] A solid-state imaging device ~~according to claim 12~~ of the amplification type, comprising,

a plurality of picture elements arranged two-dimensionally, each picture element comprising:

a semiconductor light-receiving region of a first conductivity type serving as a photoelectric conversion element, the photoelectric conversion element being disposed in a common well of a second conductivity type formed in a semiconductor substrate of the first conductivity type;

a semiconductor region of the first conductivity type serving as a source or drain of a transistor for amplification, the semiconductor region being disposed in the common well;

contacts for supplying a reference voltage to the common well, the reference voltage contacts being disposed outside the outermost picture elements and in each picture element;

a wiring connected to the reference voltage contacts for supplying a reference

voltage; and

a power source contact for supplying, to the semiconductor region of the first conductivity type, a power source voltage for driving the transistor for amplification, the power source contact being disposed in each picture element,

wherein the power source contact is connected by a wiring to a power source, the power source wiring being separate from the reference voltage wiring,

wherein one of either the reference voltage contacts or the power source contacts is connected to a wiring arranged at every row or every column of the picture elements and the other of the reference voltage contacts or the power source contacts is connected to a shielding layer having a light-receiving window formed above the wiring arranged at every row or every column of the picture elements, and

wherein the wiring arranged at every row or every column of the picture elements is connected to the reference voltage contacts and is disposed between two control lines for controlling a semiconductor element inside the picture element.

Claim 14. (Canceled)

Claim 15. (Currently Amended) [[The]] A solid-state imaging device ~~according to claim 14~~ of the amplification type, comprising,

a plurality of picture elements arranged two-dimensionally, each picture element comprising:

a semiconductor light-receiving region of a first conductivity type serving as a

photoelectric conversion element, the photoelectric conversion element being disposed in a common well of a second conductivity type formed in a semiconductor substrate of the first conductivity type, and

a semiconductor region of the first conductivity type serving as a source or drain of a transistor for amplification, the semiconductor region being disposed in the common well;

contacts for supplying a reference voltage to the common well, the reference voltage contacts being disposed outside the outermost picture elements and in each picture element;

a wiring connected to the reference voltage contacts for supplying a reference voltage; and

a power source contact for supplying, to the semiconductor region of the first conductivity type, a power source voltage for driving the transistor for amplification, the power source contact being disposed in each picture element,

wherein the power source contact is connected by a wiring to a power source, the power source wiring being separate from the reference voltage wiring,

wherein the power source contacts are connected to a shielding layer having a light-receiving window formed above the wiring for the reference voltage, and

wherein the reference voltage wiring is disposed between two control lines for controlling a semiconductor element in the picture element.

Claim 16. (Currently Amended) [[The]] A solid-state imaging device

~~according to claim 13~~ of the amplification type, comprising,

a plurality of picture elements arranged two-dimensionally, each picture element comprising:

a semiconductor light-receiving region of a first conductivity type serving as a photoelectric conversion element, the photoelectric conversion element being disposed in a common well of a second conductivity type formed in a semiconductor substrate of the first conductivity type;

a semiconductor region of the first conductivity type serving as a source or drain of a transistor for amplification, the semiconductor region being disposed in the common well;

contacts for supplying a reference voltage to the common well, the reference voltage contacts being disposed outside the outermost picture elements and in each picture element;

a wiring connected to the reference voltage contacts for supplying a reference voltage; and

a power source contact for supplying, to the semiconductor region of the first conductivity type, a power source voltage for driving the transistor for amplification, the power source contact being disposed in each picture element,

wherein the power source contact is connected by a wiring to a power source, the power source wiring being separate from the reference voltage wiring

wherein one of either the reference voltage contacts or the power source contacts is connected to a wiring arranged at every row or every column of the picture elements

and the other of the reference voltage contacts or the power source contacts is connected to a shielding layer having a light-receiving window formed above the wiring arranged at every row or every column of the picture elements,

wherein the wiring arranged at every row or every column of the picture elements is connected to the reference voltage contacts and is disposed between two control lines for controlling a semiconductor element inside the picture element,

wherein each of the picture elements further includes a transfer gate, a transistor for reset and a transistor for selection, and

wherein the two control lines are two selected from the group consisting of a control line of the transfer gate, a control line of the reset transistor and a control line of the selection transistor.

Claim 17. (Currently Amended) [[The]] solid-state imaging device ~~according to claim 11~~ of the amplification type, comprising,

a plurality of picture elements arranged two-dimensionally, each picture element comprising:

a semiconductor light-receiving region of a first conductivity type serving as a photoelectric conversion element, the photoelectric conversion element being disposed in a common well of a second conductivity type formed in a semiconductor substrate of the first conductivity type;

a semiconductor region of the first conductivity type serving as a source or drain of a transistor for amplification, the semiconductor region being disposed in the common

well;

contacts for supplying a reference voltage to the common well, the reference voltage contacts being disposed outside the outermost picture elements and in each picture element;

a wiring connected to the reference voltage contacts for supplying a reference voltage; and

a power source contact for supplying, to the semiconductor region of the first conductivity type, a power source voltage for driving the transistor for amplification, the power source contact being disposed in each picture element,

wherein the power source contact is connected by a wiring to a power source, the power source wiring being separate from the reference voltage wiring,

wherein each of the picture elements further includes a reset transistor,

wherein a reset contact for supplying a reference voltage for reset to the reset transistor is disposed in each picture element,

wherein any two of the power supply contact, the reset contact and the power source contact are connected to intersecting wirings arranged in the picture element array area, and

wherein the remaining one of the power supply contact, the reset contact and the power source contact is connected to a shielding film having a light-receiving window formed above the wiring intersecting wiring.

Claims 18-22. (Canceled)